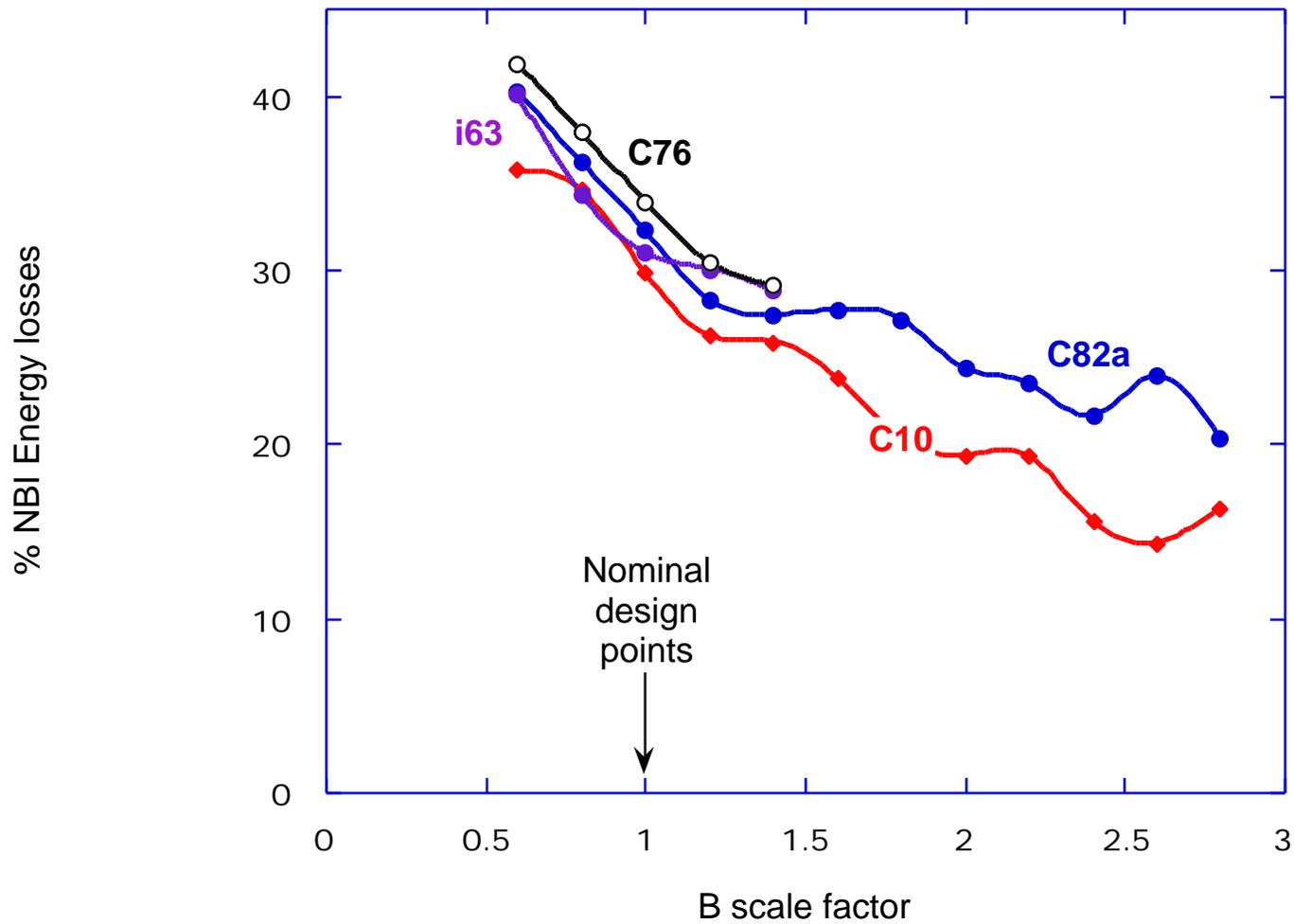


NBI Heating efficiency and I_{f} bootstrap current calculations for QA devices

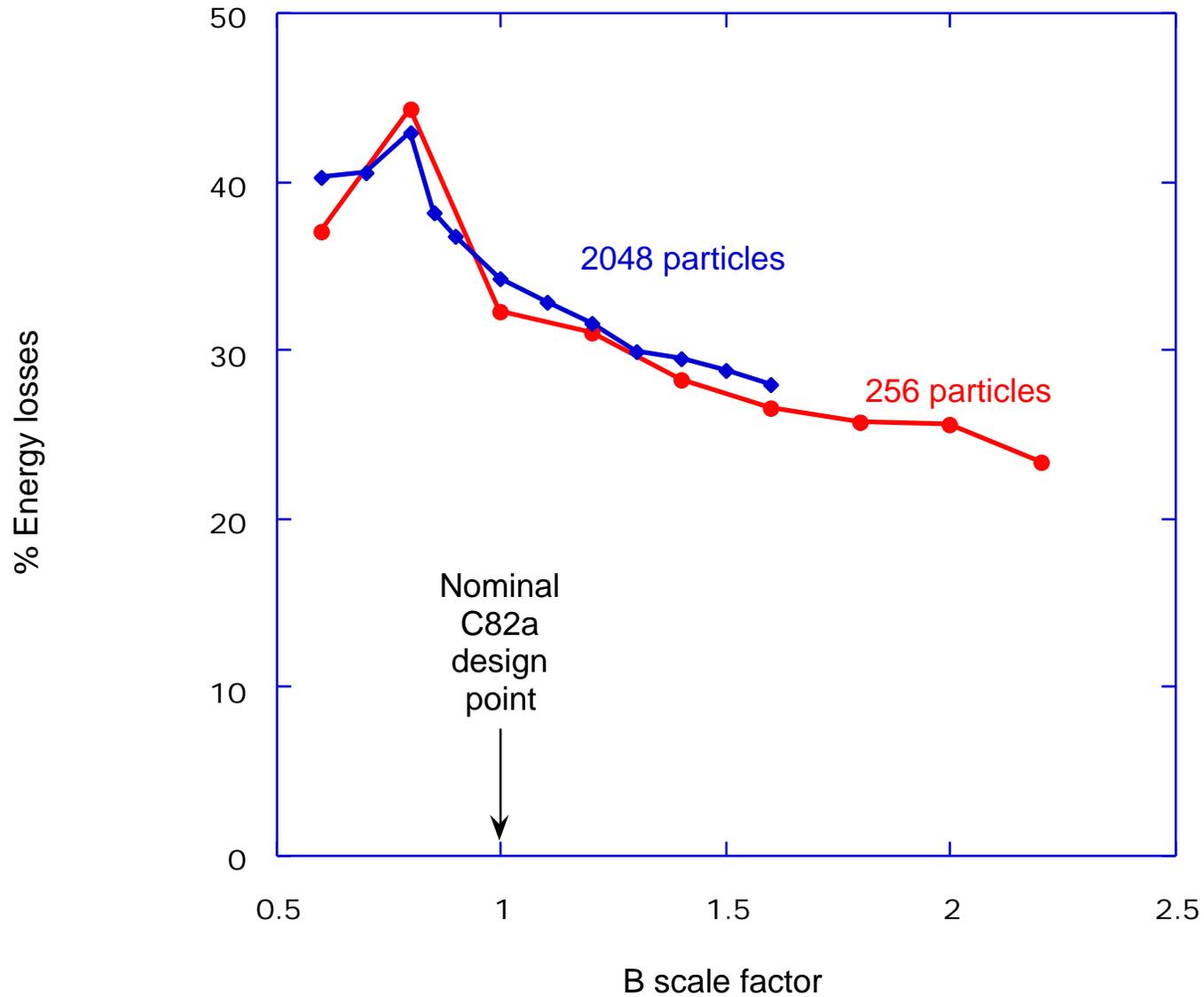
Don Spong, ORNL

- B dependence of NBI heating efficiency shows structure and deviations from I_{f}/a scaling which are caused by
 - prompt/stochastic losses
- A I_{f} calculation of bootstrap current has recently been developed based on the method of Boozer and Sasinowski
 - applied to ion currents in QA/QO devices
 - future work will look at electrons and other weighting schemes

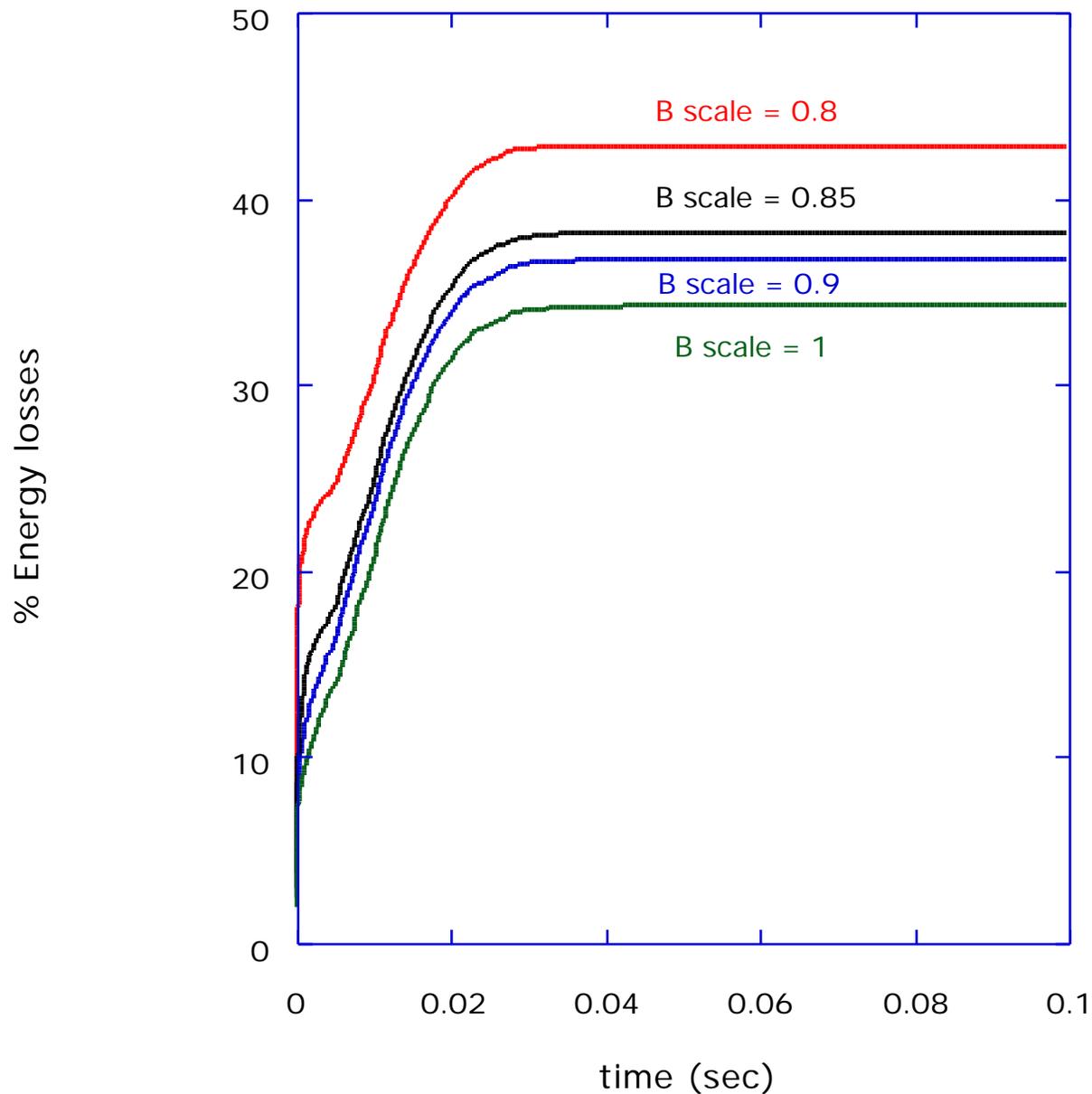
NBI energy losses for a range of QA devices at 40 keV injection energy

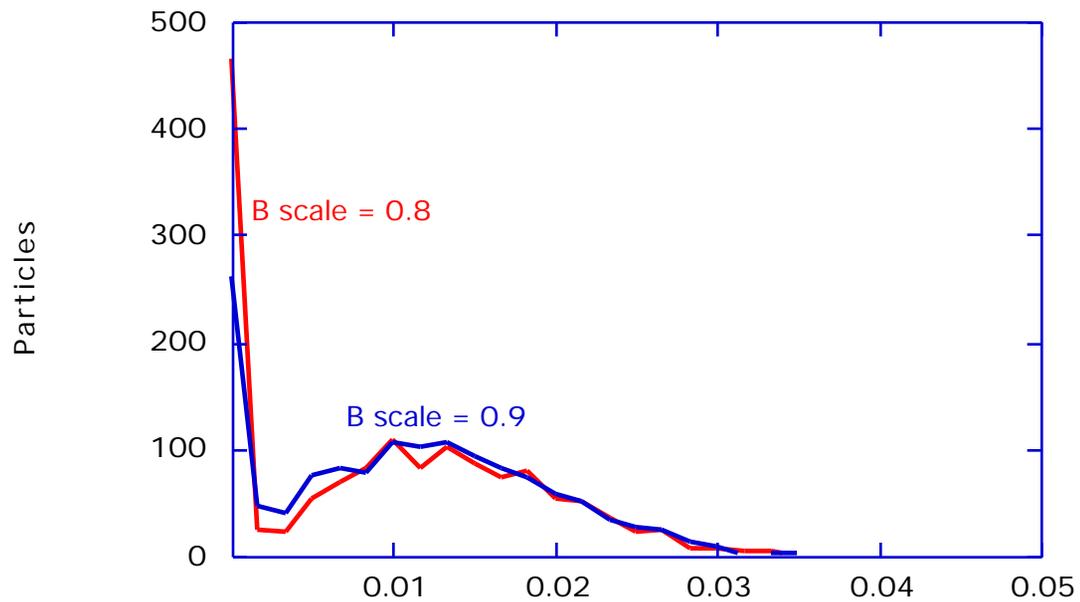


NBI losses in c82a at 50 keV injection energy

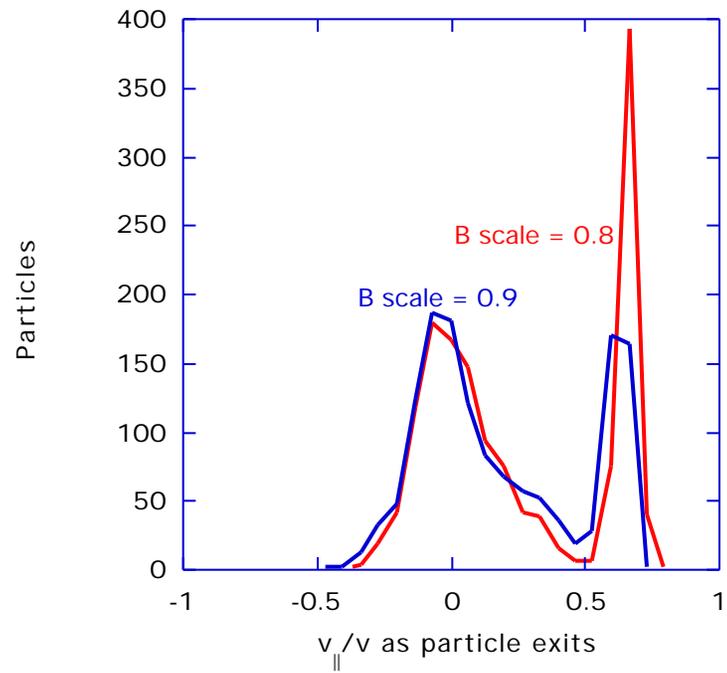
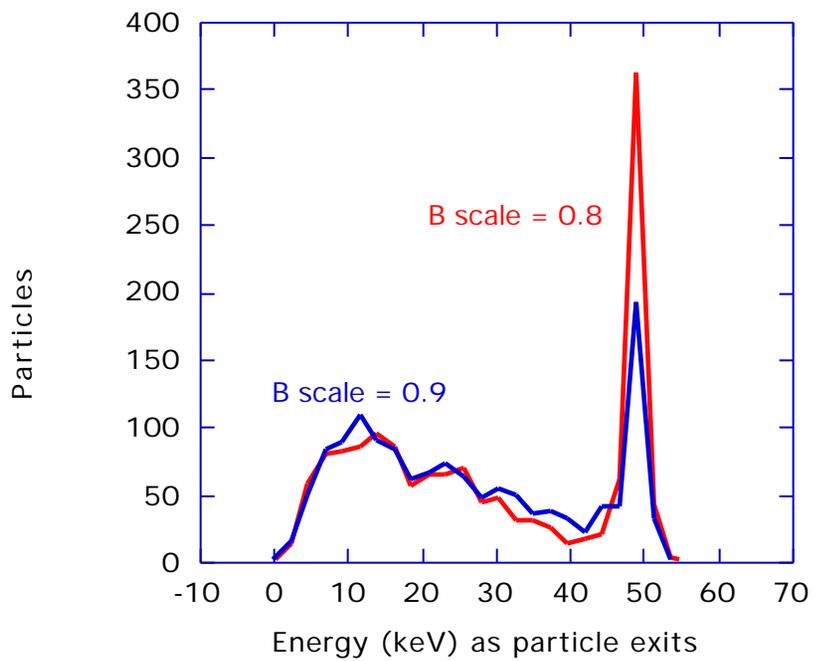


The case at 80% full field shows a higher level of prompt losses than nearby cases:

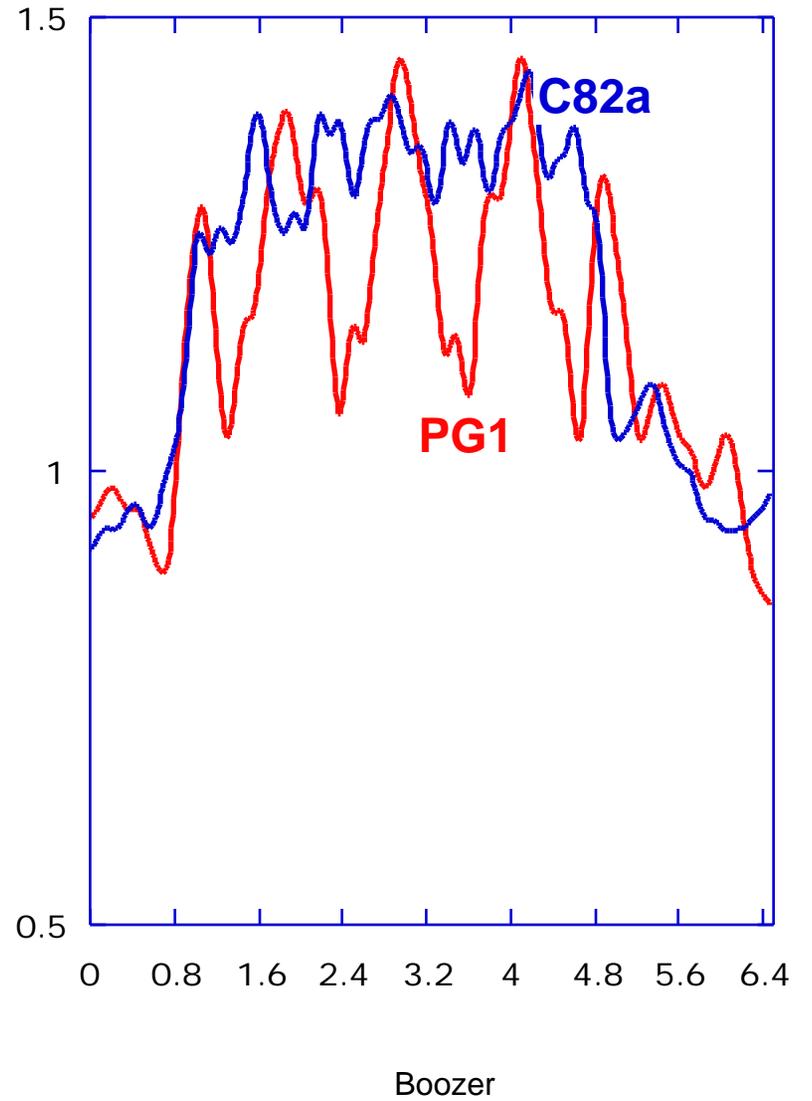
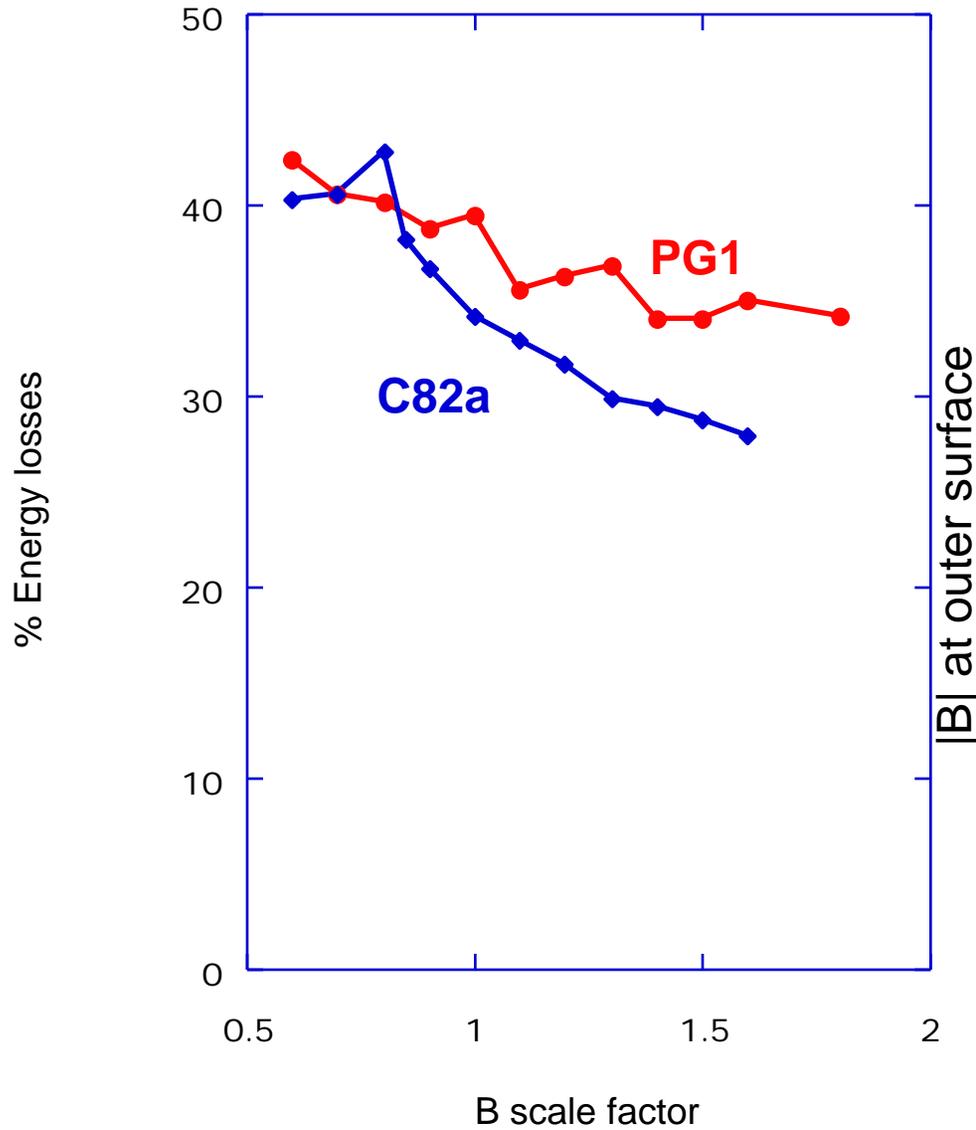




Confinement time (sec) of exiting particle

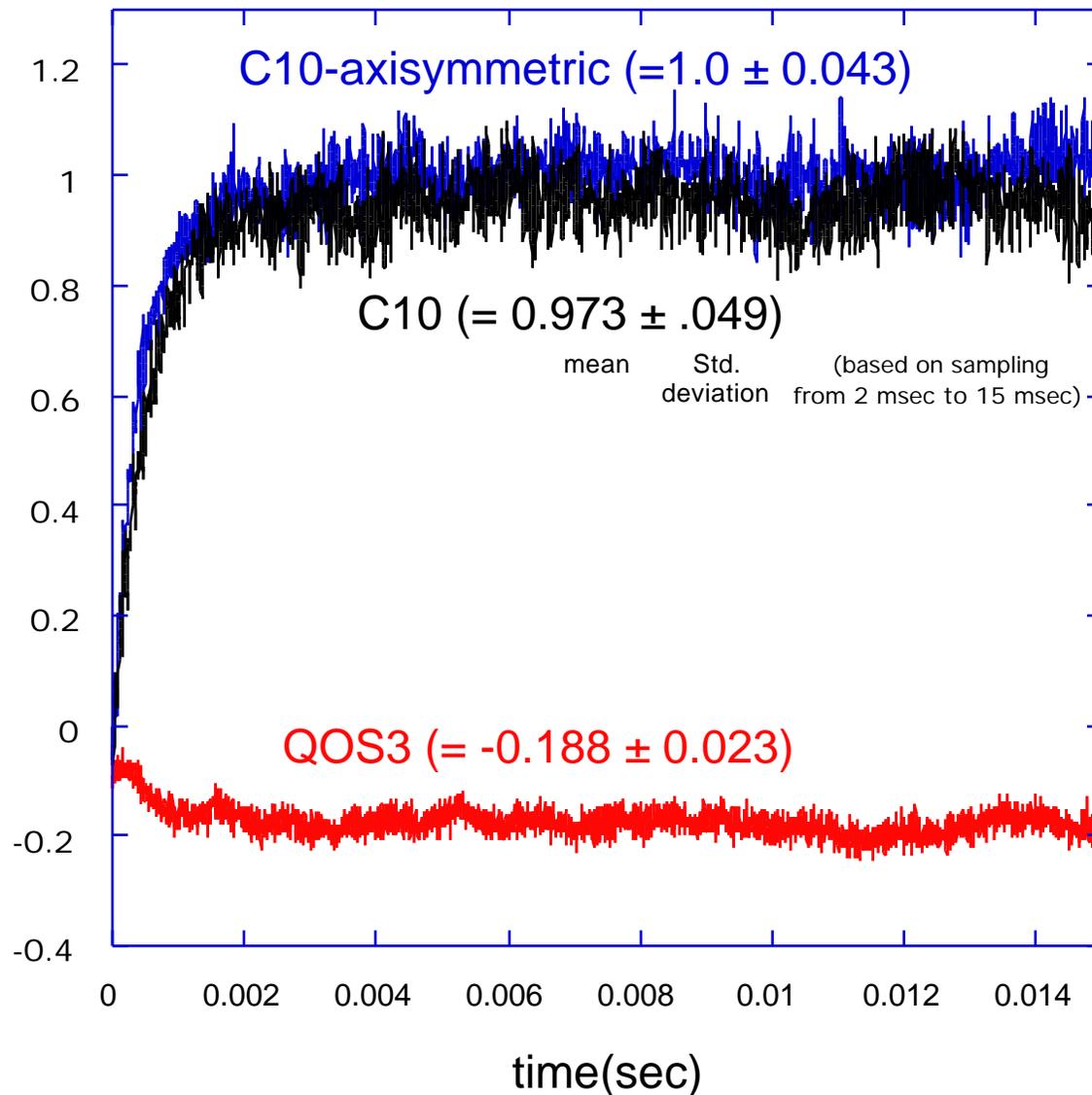


Comparison of C82a and PG1:



f bootstrap current calculations show:

- little difference between c10 and its axisymmetric limit
- expected difference in sign and magnitude between c10 and qos3



- ions, $\tau_i = 0.7\text{msec}$
- $n_0 = 3 \times 10^{13}$, $T_0 = 1 \text{ keV}$
- 4096 particles
- started at "r/a" = 0.5
- removed if $|v_{\parallel} / v_{\text{th}}| > 0.25$
- then reseeded at $v_{\parallel} = 0$